

DC to 3.5 GHz ACTIVE BIAS GAIN BLOCK

Current Barrie

Optimum Technology Matching® Applied

GaAs HBT

InGaP HBT

✓ SiGe HBT

GaAs MESFET

SiGe BiCMOS Si BiCMOS

GaAs pHEMT

Si CMOS Si BJT GaN HEMT

**RF MEMS** 

RFMD Green, RoHS Compliant, Pb-Free (Z Part Number) Package: 3x3 QFN, 16-Pin

## **Product Description**

RFMD's SGB-6433 is a high performance SiGe HBT MMIC amplifier utilizing a Darlington configuration with an active bias network. The active bias network provides stable current over temperature and process Beta variations. Designed to run directly from a 5V supply the SGB-6433 does not require a drop resistor as compared to typical Darlington amplifiers. This robust amplifier features a Class 1C ESD rating, low thermal resistance , and unconditional stability. The SGB-6433 product is designed for high linearity 5V gain block applications that require small size and minimal external components. It is on chip matched to  $50\Omega$  and an external bias

K K K

GND

NC

NC

RFIN

NC

inductor choke is required for the application band.

Active Bias

Z Z

## Features

- High Reliability SiGe HBT Technology
- Robust Class 1C ESD
- Simple and Small Size
- P<sub>1dB</sub>=18.5dBm at 1950MHz
- IP<sub>3</sub>=31dBm at 1950MHz
- Low Thermal Resistance=60C/W

## Applications

- 5V Applications
- LO Buffer Amp
- RF Pre-Driver and RF Receive Path

<b>.</b> .	Specification					
Parameter	Min.	Тур.	Max.	Unit	Condition	
Small Signal Gain		20.0		dB	850MHz	
	14.5	16.0	17.5	dB	1950MHz	
		15.0		dB	2400MHz	
Output Power at 1dB Compression		18.5		dBm	850MHz	
	16.5	18.5		dBm	1950MHz	
		17.5		dBm	2400 MHz	
Output Third Order Intercept Point		33.0		dB	850MHz	
	28.5	31.0		dB	1950MHz	
		31.0		dB	2400 MHz	
Noise Figure		4.1	5.1	dB	1950MHz	
Frequency of Operation	DC		3500	MHz		
Current	76	88	98	mA		
Input Return Loss	12.0	15.0		dB	1950MHz	
Output Return Loss	8.5	11.5		dB	1950MHz	
Thermal Resistance		60		°C/W	junction to backside	

NC

NC

RFOUT

NC

Test Conditions:  $Z_0=50\Omega$ ,  $V_{CC}=5V$ ,  $I_C=88$  mA, T=30 °C

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# rfmd 💓 QOCVO

#### **RFMD + TriQuint = Qorvo**

#### **Absolute Maximum Ratings**

Parameter	Rating	Unit
Current (I <sub>C</sub> total)	150	mA
Max Device Voltage (V <sub>D</sub> )	6.5	V
Max RF Input Power	20	dBm
Power Dissipation	0.75	W
Max Junction Temperature (T <sub>J</sub> )	150	°C
Operating Temperature Range $(T_L)$	-40 to + 85	°C
Max Storage Temperature	-40 to +150	°C

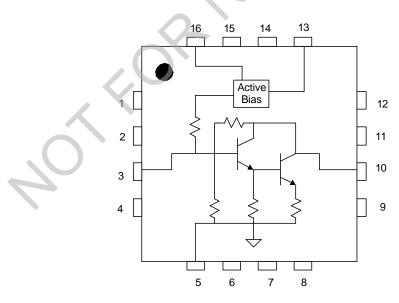
Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one. Bias Conditions should also satisfy the following expression:

 $I_D V_D < (T_J - T_L) / R_{TH}$ , j-l

#### Detailed Performance Table: V<sub>CC</sub>=5V, I<sub>C</sub>=88mA, T=25°C, Z=50 $\Omega$

Parameter	Unit	100	500	850	1950	2400	3500
		MHz	MHz	MHz	MHz	MHz	MHz
Small Signal Gain (G)	dB	21.2	20.7	20.0	16.0	15.0	12.3
Output 3rd Order Intercept Point (OIP <sub>3</sub> )	dBm		34.0	33.0	31.0	31.0	
Output Power at 1dB Compression (P <sub>1dB</sub> )	dBm		18.9	18.5	18.5	17.5	
Input Return Loss (IRL)	dB	43.6	33.3	25.6	15.0	13.8	9.7
Output Return Loss (ORL)	dB	15.8	13.9	12.2	11.5	10.2	11.3
Reverse Isolation (S <sub>12</sub> )	dB	24.4	24.6	25.0	24.4	23.8	22.5
Noise Figure (NF)	dB	5.1	3.6	3.6	4.1	4.6	5.2

#### **Simplified Device Schematic**





Caution! ESD sensitive device.

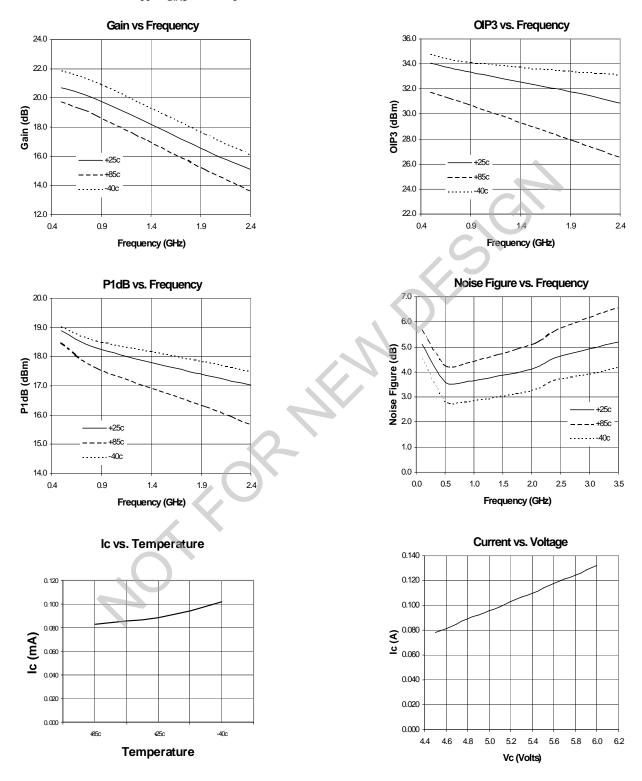
Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical perfor-mance or functional operation of the device under Absolute Maximum Rating condi-tions is not implied.

RoHS status based on EUDirective2002/95/EC (at time of this document revision).

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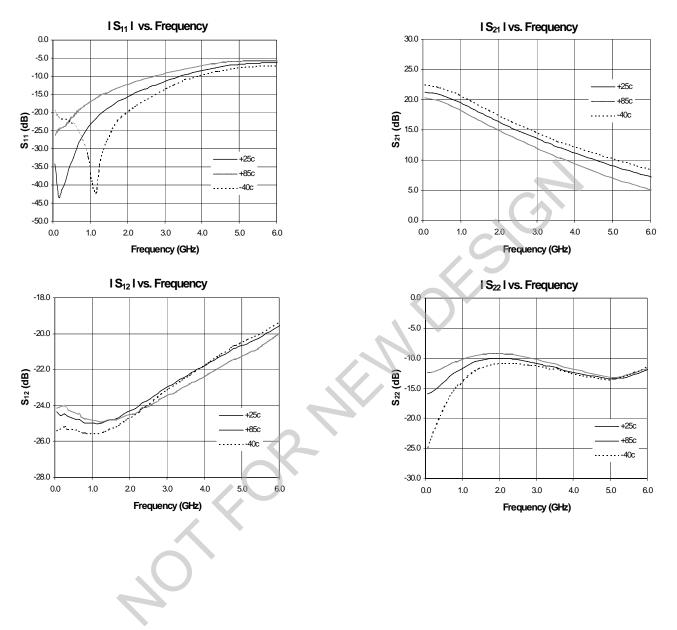


#### Evaluation Board Data ( $V_{CC} = V_{BIAS} = 5.0V$ , $I_C = 88$ mA) Bias Tee substituted for DC feed inductor (L1)



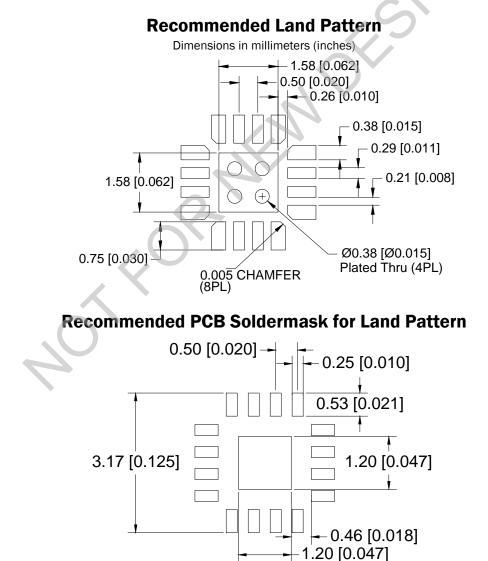


### Evaluation Board Data ( $V_{CC}=V_{BIAS}=5.0V$ , $I_{C}=88$ mA) Bias Tee substituted for DC feed inductor (L1) cont



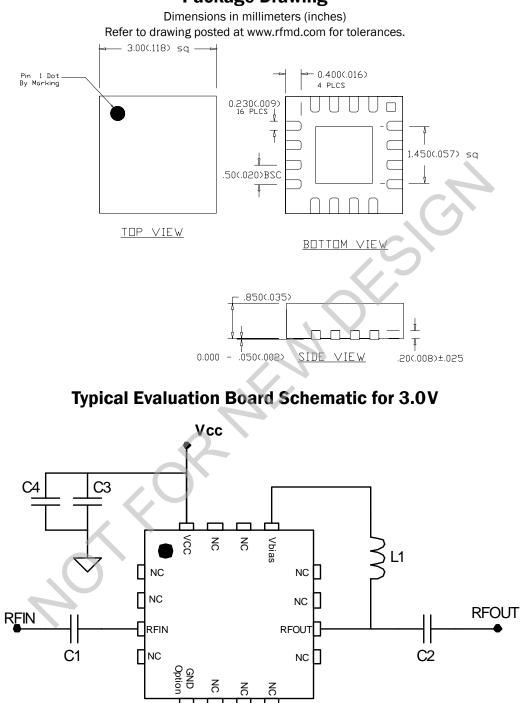


Pin	Function	Description		
1, 2,	NC	These are no connect pins. Leave them unconnected on the PC board.		
4, 6,				
7, 8,				
11,				
12, 14				
3	RF IN	RF input pin. A DC voltage should not be connected externally to this pin		
5	GND	An extra ground pin that is connected to the backside exposed paddle. Connection is optional.		
10	RF OUT	RF Output pin. Bias is applied to the Darlington stage thru this pin.		
13	VBIAS	This pin sources the current from the active bias circuit. Connect to pin 10 thru an inductor choke.		
16	VCC	This is Vcc for the active bias circuit.		
Back-	GND	GND The backside exposed paddle is the main electrical GND and requires multiple vias in the PC board to GND. It is also the main the provide the main electrical GND and requires multiple vias in the PC board to GND.		
side		main thermal path.		







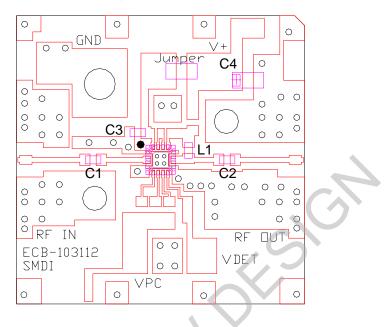


## **Package Drawing**





## **Evaluation Board Layout and Bill of Materials**



Board material GETEK, 31 mil thick, Dk=4.2, 1oz copper

#### Component Values By Band

Designator	500 MHz	850 MHz	1950 MHz	2400MHz	
C3	1000pF	1000pF	1000 pF	1000pF	
C4*	1uF	1uF	1uF	1uF	
C1, C2	220pF	68 pF	43pF	22pF	
L1	68 nH	33nH	22nH	18nH	

\*C4 is optional depending on application and filtering. Not required for SGB device operation.

Note: The amplifier can be run from a 8V supply by simply inserting a 33 $\Omega$  resistor in series with V<sub>CC</sub>.

### **Part Identification**

The part will be symbolized with an "SGB6433" for Sn/Pb plating or "SGB64Z" for RoHS green compliant product. Marking designator will be on the top surface of the package.

## **Ordering Information**

Part Number	Reel Size	Devices/Reel
SGB-6433	13"	3000
SGB-6433Z	13"	3000





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